

ABSTRACT OF THE DISCLOSURE

Fuse circuits based on a single flash cell or floating-gate memory cell are adapted for use in memory devices, particularly in low-voltage, flash memory applications. The fuse circuits include a floating-gate memory cell for storing a data value and a fuse latch to hold and transfer the data value of the floating-gate memory cell at power-up or upon request. A latch driver circuit can write data values to the fuse latch without affecting the data value stored in the floating-gate memory cell. The fuse circuits can further utilize the same structure, pitch, bit-line organization and word-line organization as the memory device's memory array. As the fuse circuits can utilize the same structure and organization, the data value of the fuse circuit can be programmed, erased and read using the same data path as the regular memory array.